

ES3DGB THRU ES3JGB

3.0AMPS. GLASS PASSIVATED SUPER FAST RECTIFIER

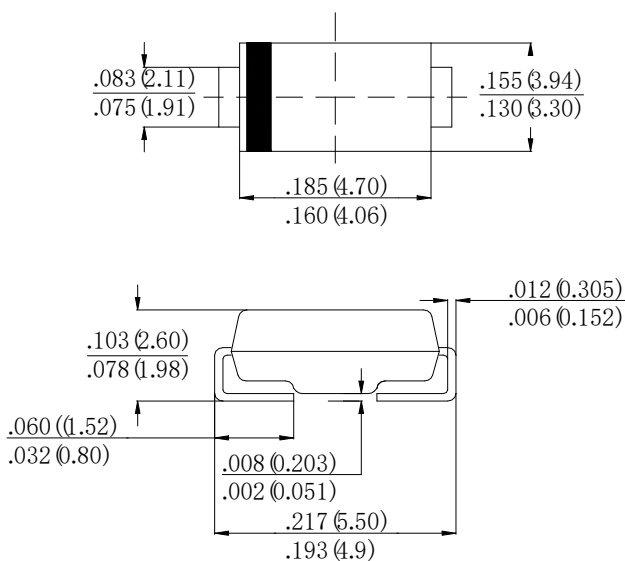
FEATURE

- . High current capability
- . Low forward voltage drop
- . Low power loss, high efficiency
- . High surge capability
- . High temperature soldering guaranteed
260°C/10 seconds at terminals.
- . Superfast recovery time for high efficiency
- . For surface mounted application.
- . Easy pick and place.

MECHANICAL DATA

- . Case: Molded plastic
- . Epoxy: UL94V-0 rate flame retardant
- . Lead: MIL-STD- 202E, Method 208 guaranteed
- . Polarity:Color band denotes cathode end
- . Mounting position: Any

SMB (DO-214AA)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

Type Number	SYM BOL	ES3DGB	ES3GGB	ES3JGB	units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	200	400	600	V
Maximum RMS Voltage	V_{RMS}	140	280	420	V
Maximum DC blocking Voltage	V_{DC}	200	400	600	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	3.0			A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	90.0			A
Maximum Forward Voltage at 3.0A DC	V_F	0.95	1.3	1.7	V
Maximum DC Reverse Current @TJ =25°C at rated DC blocking voltage @TJ =125°C	I_R	5.0 200.0			μA
Maximum Reverse Recovery Time (Note 1)	t_{rr}	35			nS
Typical Junction Capacitance (Note 2)	C_J	50	25		pF
Typical Thermal Resistance (Note 3)	$R_{(JA)}$	60			°C /W
	$R_{(JL)}$	12			
	$R_{(JC)}$	15			
Storage Temperature	T_{STG}	-55 to +150			°C
Operation Junction Temperature	T_J	-55 to +150			°C

Note:

1. Reverse Recovery test Condition: If=0.5A,IR=1.0A,IRR=0.25A
2. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
3. Measured on P.C.Board with 0.6×0.6"(15.0×15.0mm)Copper Pad Areas.

RATING AND CHARACTERISTIC CURVES

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

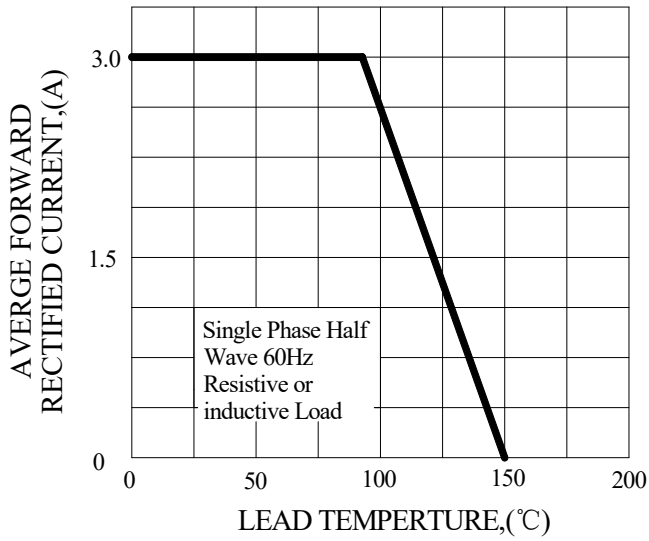


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

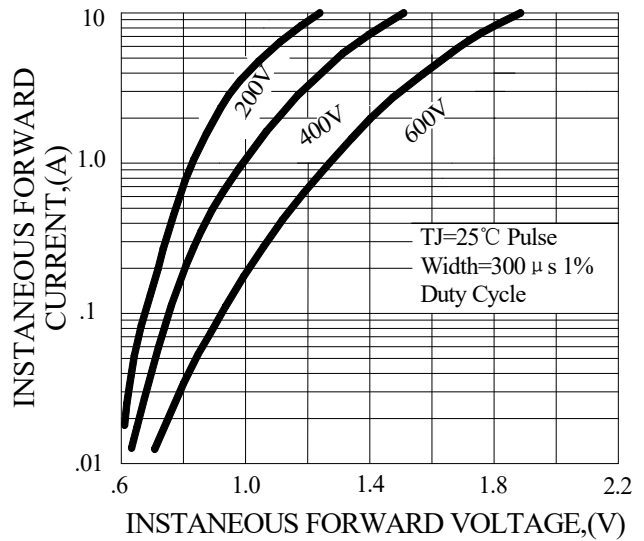


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

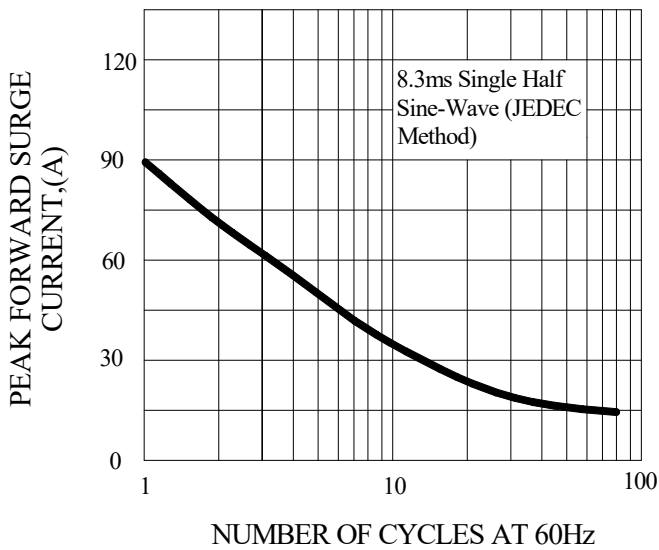


FIG.4-TYPICAL REVERSE CHARACTERISTICS

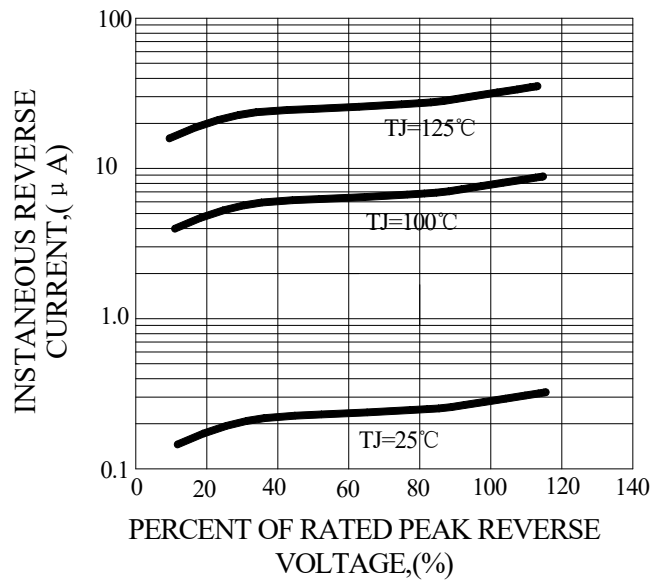
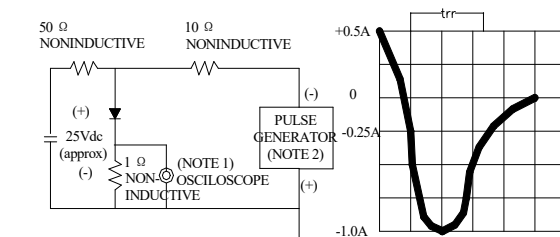


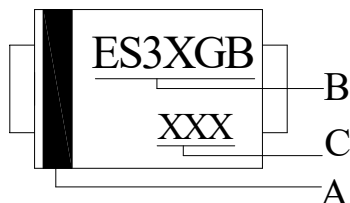
FIG.5-TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1. Rise Time=7ns max, Input Impedance= 1 megohm, 22pF.
2. Rise Time=10ns max, Source Impedance= 50 ohms.

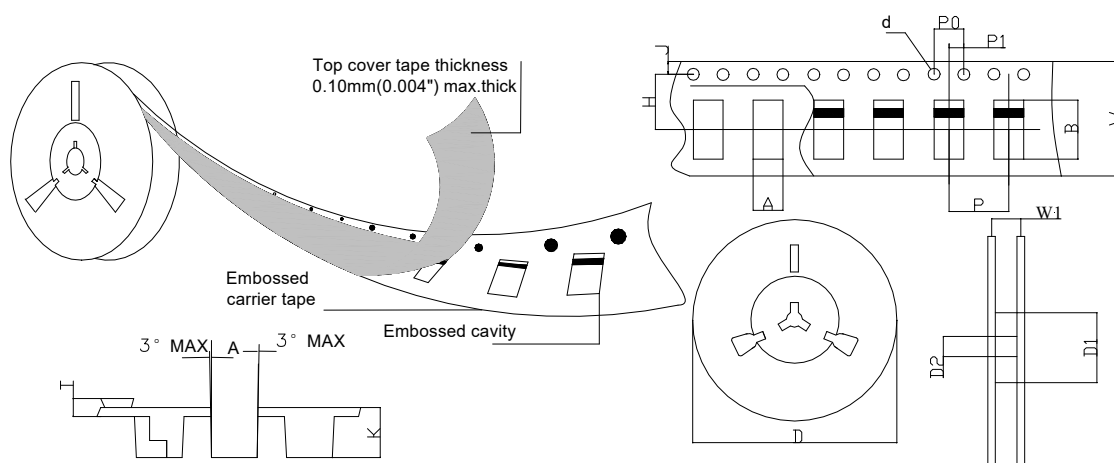
Marking and packaging illustration

1、Marking



SYMBOL	Explanation
A	Color Band Denotes Cathode
B	Product Name
C	Date Code

2、Packaging



SPECIFICATIONS mm(inch)		PACKAGE	SPECIFICATIONS mm(inch)		PACKAGE
ITEM	SYM BOL	SMB (DO-214AA)	ITEM	SYM BOL	SMB (DO-214AA)
Carrier width	A	3.81(0.150)Max	Carrier depth	K	2.45(0.965)Typ
Carrier length	B	5.41(0.213)Max	Punch hole pitch	P	8.00(0.315)Typ
Sprocket hole	d	ø1.55(0.061)Typ	Sprocket hole pitch	P0	4.00(0.157)Typ
Reel outer diameter	D	330.0(13.0)Typ	Embossment center	P1	2.00(0.079)Typ
Reel inner diameter	D1	50.0(1.969)Min	Overall tape thickness	T	0.30(0.012)Typ
Feed hole diameter	D2	13.0(0.512)Typ	Tape width	W	12.0(0.472)Typ
Sprocket hole position	J	1.75(0.069)Typ	Reel width	W1	12.4(0.488)Min
Punch hole position	H	5.55(0.219)Typ			